

a basic substrate;
a conductive ground electrode that is placed on the basic structure;
a variable impedance material that is placed on a portion of the conductive ground electrode;
an insulation layer that is placed on the variable impedance material and exposes a partial area of the variable impedance material; and
a conductive signal electrode that is placed on the insulation layer and the exposed variable impedance material and connects with the variable impedance material.

23(New). The transient voltage suppressor structure as claimed in claim 22, wherein the basic substrate is a glass.

24(New). The transient voltage suppressor structure as claimed in claim 22, wherein the basic substrate is a ceramic material.

25(New). The transient voltage suppressor structure as claimed in claim 22, wherein a contact face exists between the variable impedance material and the signal electrode to conduct the transient voltage to the ground electrode.

26(New). The transient voltage suppressor structure as claimed in claim 22, wherein the insulation layer can prevent the point discharge occurring on the edge of the signal electrode.

27(New). The transient voltage suppressor structure as claimed in claim 22, wherein the insulation layer is made from a material with low dielectric constant which is an oxide or metallic oxide.

28(New). The transient voltage suppressor structure as claimed in claim 22, wherein the structure of the insulation layer conforms to the profile of the variable impedance material.

29(New). A transient voltage suppressor structure applicable to electronic components which includes:

- a basic substrate;
- a signal electrode and a ground electrode that are placed on the basic substrate;
- an insulation layer that is placed on the basic substrate between the signal electrode and the ground electrode;
- a variable impedance material that is placed on the insulation layer between the signal electrode and the ground electrode and connects with the signal electrode and the ground electrode through the variable impedance material.

30(New). The transient voltage suppressor structure as claimed in claim 29, wherein the basic substrate is a glass or a ceramic basic substrate.

31(New). The transient voltage suppressor structure as claimed in claim 29, wherein a contact face exists between the variable impedance material and the signal electrode to conduct the transient voltage to the ground electrode.

32(New). The transient voltage suppressor structure as claimed in claim 29, wherein the insulation layer covers the edge of the signal electrode to prevent the effect of the point discharge occurring on the edge of the signal electrode.

33(New). The transient voltage suppressor structure as claimed in claim 29, wherein the insulation layer is made from material with low dielectric constant which is an oxide or metallic oxide.

34(New). A transient voltage suppressor structure applicable to electronic components which includes:

- a basic substrate;
- a signal and ground electrode placed on the basic substrate;
- an insulation layer placed between the signal electrode and the ground electrode;

a variable impedance material placed between the signal electrode and the ground electrode;

the characteristics of the said transient voltage suppressor structure lie in that the edge of the signal electrode is covered by the insulation layer and the transient voltage is conducted to the ground electrode through the contact face of the variable impedance material and the signal electrode.

35(New). The transient voltage suppressor structure as claimed in claim 34, wherein the variable impedance material is placed on one end of the ground electrode, while the insulation layer is placed on the edge of the variable impedance material and exposes the central part of the variable impedance material. One end of the signal electrode is placed on the insulation layer and the exposed variable impedance material.

36(New). The transient voltage suppressor structure as claimed in claim 34, wherein the insulation layer is formed in a box structure.

37(New). The transient voltage suppressor structure as claimed in claim 35, wherein the insulation layer is formed in a box structure.

38(New). The transient voltage suppressor structure as claimed in claim 34, wherein the structure of the insulation layer is in conformity with the profile of the variable impedance material.

39(New). The transient voltage suppressor structure as claimed in claim 35, wherein the structure of the insulation layer is in conformity with the profile of the variable impedance material.

40(New). The transient voltage suppressor structure as claimed in claim 34, wherein the insulation layer is placed on the basic substrate between the signal electrode and the ground electrode to cover the signal electrode, while the variable

impedance material is placed on the insulation layer between the signal electrode and the ground electrode and connects with the signal electrode and the ground electrode electrically.

41(New). The transient voltage suppressor structure as claimed in claim 34, wherein the basic substrate is a glass or ceramic basic substrate.

42(New). The transient voltage suppressor structure as recited in claim 34, wherein the insulation layer is made from a material with low dielectric constant which is an oxide or metallic oxide.